

ABSTRACT

Ag ALLOY BONDING WIRE FOR SEMICONDUCTOR DEVICE

An object of the present invention is to provide an Ag alloy bonding wire for a semiconductor device capable of extending the high-temperature life of a wire, reducing chip damage during ball bonding, and improving characteristics such as ball bonding strength in applications of on-vehicle memory devices. The Ag alloy bonding wire for a semiconductor device according to the present invention contains one or more of In and Ga for a total of 110 at ppm or more and less than 500 at ppm, and one or more of Pd and Pt for a total of 150 at ppm or more and less than 12,000 at ppm, and a balance being made up of Ag and unavoidable impurities.

[No figure]